

Radar Pulsed Power Transistor 30W, 1.2-1.4 GHz, 1ms Pulse, 10% Duty M/A-COM Products Released, 30 May 07

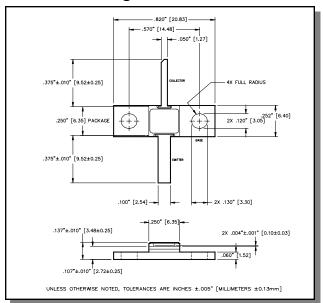
Features

- · NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- · High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	56	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ic	3.0	Α
Power Dissipation @ +25°C	P _{TOT}	115	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 60mA		BV _{CES}	56	-	V
Collector-Emitter Leakage Current	V _{CE} = 28V		I _{CES}	-	3.0	mA
Thermal Resistance	Vcc = 28V, Pout = 30W	F = 1.2, 1.3, 1.4 GHz	R _{TH(JC)}	-	1.5	°C/W
Output Power	Vcc = 28V, Pout = 30W	F = 1.2, 1.3, 1.4 GHz	P _{IN}	-	4.9	W
Power Gain	Vcc = 28V, Pout = 30W	F = 1.2, 1.3, 1.4 GHz	G _P	7.8	-	dB
Collector Efficiency	Vcc = 28V, Pout = 30W	F = 1.2, 1.3, 1.4 GHz	ης	50	-	%
Input Return Loss	Vcc = 28V, Pout = 30W	F = 1.2, 1.3, 1.4 GHz	RL	-	-10	dB
Load Mismatch Tolerance	Vcc = 28V, Pout = 30W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	Vcc = 28V, Pout = 30W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

ADVANCED: Data Sheets contain information regarding a product M/A-COM is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

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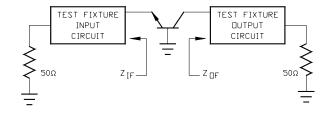


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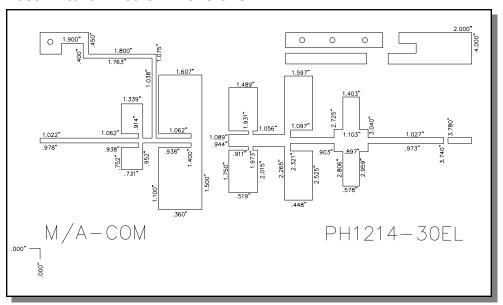
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RF Test Fixture Impedance

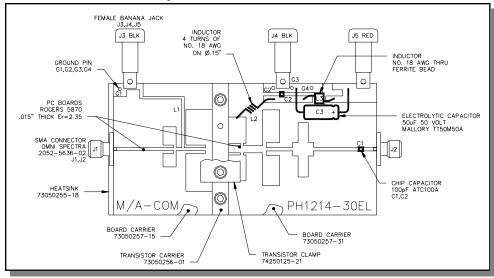
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1.2	2.5 - j3.5	10.5 + j2.0
1.3	2.7 - j2.7	6.3 + j2.0
1.4	3.5 - j3.5	5.3 + j1.5



Test Fixture Circuit Dimensions



Test Fixture Assembly



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